

COMPLEMENTARY SILICON PLASTIC POWER TRANSISTORS

... designed for use in general purpose amplifier and switching application.

FEATURES:

- * Collector-Emitter Sustaining Voltage-
- V_{CEO(sus)}=100V (Min.)
- * DC Current Gain hFE =25 (Min) @ I_C=1.5A
- * Current Gain-Bandwidth Product $f_T=3.0$ MHz (Min) @ $I_C=1.0A$

25 AMPERES COMPLEMENTARY SILICON POWER TRANSISTOR 100 VOLTS 125 WATTS

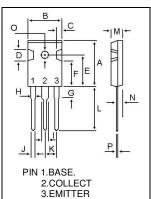
PNP

TIP36C

MAXIMUM RATINGS

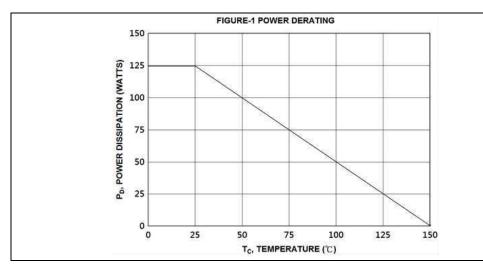
Characteristic	Symbol	TIP36C	Unit
Collector-Emitter Voltage	V _{CEO}	100	V
Collector-Base Voltage	V _{CBO}	100	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current-Continuous Peak	I _С I _{СМ}	25 40	А
Base Current	IB	5.0	А
Total Device Dissipation @ T _C =25°C Derate above 25°C	PD	125 1.0	Watts W/ºC
Operating and Storage Junction Temperature Range	T _J , T _{STG} -65 to +150		°C

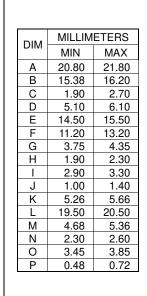
TO-247(3P)



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.0	°C/W





ELECTRICAL CHARATERISTICS (T_c=25^oC unless otherwise noted)

Characteristic	Symbol	Min.	Max	Unit	
OFFCHARACTERISTICS					
Collector-Emitter Sustaining Voltage ($I_C = 30 \text{ mAdc}, I_B = 0$)	V _(SUS) CEO	100		v	
Collector Cutoff Current ($V_{CE} = 60 V$, $I_{B}= 0$)	I _{CEO}		1.0	mA	
Collector Cutoff Current (V_{CE} = 100 V, V_{BE} = 0)	I _{CES}		0.7	mA	
Emitter Cutoff Current (V_{BE} = 5.0 V, I _c = 0)	I _{EBO}		1.0	mA	

ON CHARACTERISTICS(1)

DC Current Gain ($I_C = 1.5 A, V_{CE} = 4.0 V$) ($I_C = 15 A, V_{CE} = 4.0 V$)	h _{FE}	25 15	75	
Collector-Emitter Saturation Voltage ($I_C = 15 \text{ A}, I_B = 1.5 \text{ A}$) ($I_C = 25 \text{ A}, I_B = 5.0 \text{ A}$)	V _{CE(sat)}		1.8 4.0	V
Base-Emitter On Voltage ($I_C = 15 \text{ A}, V_{CE} = 4.0 \text{ V}$) ($I_C = 25 \text{ A}, V_{CE} = 4.0 \text{ V}$)	$V_{BE(on)}$		2.3 5.0	V

DYNAMIC CHARATERISTICS

Current gain-Bandwidth product (I _C =500 mA ,V _{CE} =10 V, f _{TEST} =1MHz	f⊤	3.0	MHz
Small Signal Current Gain (I _C =1.0 A, V _{CE} =10 V, f=1 kHz)	h _{fe}	25	

(1) Pulse test: Pulse Width \leq 300 us, Duty Cycle \leq 2.0%

(2) $f_{T=} I h_{fe} I \circ f_{TEST}$



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